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Application Number	09/945512
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2812
Examiner Name	Booth, Richard

Sheet 1 of 2

Attorney Docket No: 1303.027US1

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Complete if Known Application Number Filing Date First Named Inventor Group Art Unit Examiner Name	09/945512
	August 30, 2001
	Forbes, Leonard
	2812
	Booth, Richard
Sheet 2 of 2	Attorney Docket No: 1303.027US1

OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS			
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